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(54) Title: METHOD OF PRODUCING A RESIST STRUCTURE WITH UNDERCUT SIDEWALL

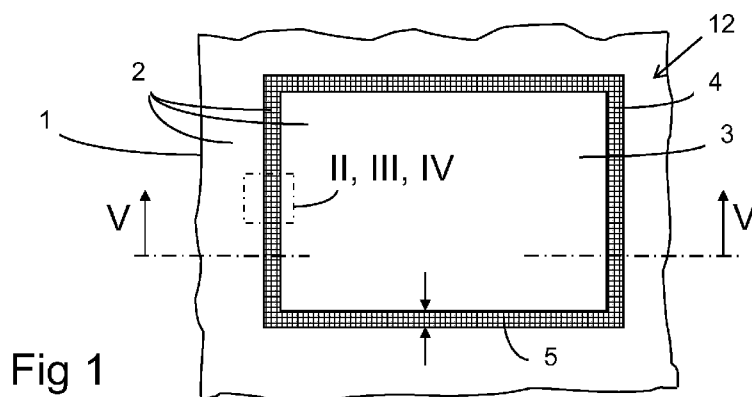


Fig 1

(57) Abstract: The method comprises the steps of applying a layer of a negative photoresist (2) on a bottom layer (1), providing the layer of the negative photoresist with a pattern arranged in a border zone (4) of the resist structure (3) to be produced, irradiating a surface area of the layer of the negative photoresist according to the resist structure to be produced, and removing the layer of the negative photoresist outside the irradiated surface area. The pattern is produced in such a manner that it comprises a dimension that is smaller than a minimal resolution of the irradiation. The pattern may especially be designed as a sub-resolution assist feature.

Description

METHOD OF PRODUCING A RESIST STRUCTURE WITH UNDERCUT SIDEWALL

- 5 In semiconductor technology photolithography is applied to structure a photoresist layer to be used as a mask. The photoresist layer is irradiated by a light source through openings in an opaque mask, which are shaped according to the pattern that is to be transferred to the photoresist layer.
- 10 The photoresist is then treated with a developer solution. When a positive photoresist is used, the developer dissolves and removes the regions of the photoresist that have been exposed to light. When a negative photoresist is used, the developer dissolves and removes the regions of the
- 15 photoresist that have not been exposed to light.

- The absorption of incident light by a layer of negative photoresist decreases exponentially with the distance from the layer surface and does practically not change during the
- 20 illumination. As the solubility of the negative photoresist is reduced according to the dose of radiation absorbed, the illumination yields a vertical profile of the solubility, which increases with increasing distance from the layer surface. The developer that is subsequently applied dissolves
- 25 the entire region of the negative photoresist that has not been illuminated together with a lower layer portion of the illuminated region, whereas the photoresist is not dissolved at the surface of the illuminated region. An undercut is thus produced in the sidewall of the remaining photoresist
- 30 structure. Negative photoresist is therefore especially suitable to produce structures with overhanging upper edges and with a reentrant sidewall profile.

- 2 -

The shape of the undercut depends on parameters of the developing process, in particular its duration and the temperature and amount of the developer, which can be controlled during the process. A minimal developing time is
5 required to remove the photoresist completely from the area that has not been illuminated, which is the reason for a minimal size of the sidewall undercut. Furthermore, the developing progress is different for dense and isolated structures, and the sizes of the respective undercuts will
10 differ correspondingly. Another problem arises from the fact that the insoluble upper layer portion rests on a relatively soft and thermally instable lower layer portion of the photoresist, which may later cause a degradation of the intended pattern under elevated temperatures, unless the
15 whole photoresist layer is stabilized by a flood exposure.

Lift-off methods are applied to produce a structured layer, especially a structured metal layer, on a surface of a semiconductor device. Regions of the surface that are not to
20 be occupied by the structured layer are covered with a sacrificial layer. An entire metal layer is applied on the bare areas of the surface and on the sacrificial layer, which is subsequently removed together with the overlying portion of the metal. After this lift-off, the remaining metal forms
25 the structured layer. For this method to be feasible, the portion of the metal overlying the sacrificial layer must be separable from the rest of the metal layer. This is facilitated by an overhanging flank with a sharp upper edge of the sacrificial layer, so that the undercut sidewall of
30 the sacrificial layer has a reentrant profile with negative slope. A conformal deposition of the metal is prevented by the sharp edge, where the metal layer is interrupted.

US 4,024,293 A discloses a high sensitivity electron resist system for lift-off metallization. Resist films are formed by at least two layers of different radiation degradable organic polymers, which are developable by different solvents. One of the layers comprises a co-polymer of polymethyl methacrylate (PMMA) and methacrylic acid (MAA). The other layer is pure polymethyl methacrylate. The developer used for one of the layers does not attack the other layer even in areas that have been exposed to high-energy radiation, and vice versa.

10

US 4,104,070 A discloses a method of making a negative photoresist image. A photoresist layer containing 1-hydroxyethyl-2-alkyl-imidazoline is exposed to actinic radiation according to the pattern to be produced. The photoresist is heated and subjected to a blanket exposure to actinic radiation. The portion of the photoresist that had not already been exposed previously is then removed with a solvent to yield a negative image.

15

US 4,564,584 A discloses a photoresist lift-off process for fabricating self-aligned structures in semiconductor devices. A layer of a negative photoresist is applied on a structured layer of a positive photoresist. The entire structure is exposed to light, and the negative photoresist is thus rendered insoluble. Since the upper photoresist layer is at least translucent to the light, the remaining portions of the positive photoresist become soluble. They are removed together with the overlying portions of the negative photoresist. The remaining portions of the negative photoresist form a structured photoresist mask. This method provides a complete, mutually self-aligned image reversal of the patterns of the first and second photoresist layers.

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US 5,654,128 A discloses a single resist layer lift-off process for forming patterned layers on a substrate. The extent of the penetration of chlorobenzene into the resist layer is controlled by a post-soak bake. A post-metallization
5 bake is employed to improve lift-off. The resist profile is provided with an increased overhang length and a negative slope of the sidewalls in order to prevent the sidewalls of the resist from being metallized and to facilitate the removal of the resist by lift-off.

10

US 7,141,338 B2 discloses sub-resolution assist features (SRAF). In an image printed on a substrate, corner rounding and image shortening is reduced by illuminating a photolithographic mask and projecting light transmitted
15 through the mask onto the substrate using an optical projection system. The mask has a pattern that includes at least one printable feature having at least one corner. A line feature is incorporated in the mask pattern in close proximity to a corresponding corner of the printable feature
20 and has a line width that is smaller than a minimum resolution of the optical projection system.

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US 7,694,269 B2 discloses a method for selectively positioning sub-resolution assist features (SRAF) in a photomask pattern for an interconnect. The method comprises
determining if a first interconnect pattern option, which is designed to be formed with SRAF, will yield a better circuit performance than a second interconnect pattern option, which is designed to be formed without SRAF. If the first option is
30 preferred, one or more SRAF patterns are positioned to facilitate patterning. Otherwise the second option is selected as a target pattern and no SRAF is provided.

It is an object of the present invention to provide a method for producing a resist structure having an undercut sidewall such that the method obviates the problems mentioned above and is particularly useful for producing a lift-off mask.

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This object is achieved with the method of producing a resist structure according to claim 1. Variants derive from the dependent claims.

10 The method for producing a resist structure allows the formation of a three-dimensional structure of negative photoresist by an implementation of layout-features below the resolution limit of the imaging system that is used for the irradiation of the photoresist.

15

The method comprises the steps of applying a layer of a negative photoresist on a bottom layer, providing the layer of the negative photoresist with a pattern arranged in a border zone of the resist structure to be produced,

20 irradiating a surface area of the layer of the negative photoresist according to the resist structure to be produced, and removing the layer of the negative photoresist outside the irradiated surface area. The pattern is produced in such a manner that it comprises a dimension or structural feature
25 that is smaller than a minimal resolution of the irradiation. The pattern may especially be provided as a sub-resolution assist feature. The pattern is formed within the layer of the negative photoresist.

30 In a variant of the method, at least one dimension characterizing the pattern is smaller than one tenth of a width of the border zone.

In a further variant of the method, the pattern is produced such that it comprises a plurality of elements having the same dimensions.

5 In a further variant of the method, the pattern is produced such that it comprises a plurality of elements having the same dimensions, which are smaller than one tenth of a width of the border zone.

10 In a further variant of the method, the elements of the pattern are arranged in a regular array with constant pitch.

In a further variant of the method, the elements of the pattern are arranged in a regular array with a constant
15 pitch, which is smaller than one tenth of a width of the border zone.

In further variants of the method, the pattern is a gridlike pattern, a pattern of parallel lines or a pattern of contact
20 holes.

The method can especially be applied to produce a resist structure with an undercut sidewall formed in the region of the border zone, in particular a resist structure that is
25 provided as a lift-off mask.

The following is a detailed description of examples of the method in conjunction with the appended figures.

30 Figure 1 is a top view of a layer of negative photoresist indicating the location of the resist structure to be produced.

Figure 2 is a magnified view of the section indicated in Figure 1 for a variant using a grid-like pattern arranged in a border zone of the resist structure.

5 Figure 3 is a magnified view according to Figure 2 for a further variant using a pattern of parallel lines.

Figure 4 is a magnified view according to Figure 2 for a further variant using a pattern of contact holes.

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Figure 5 is a cross section showing a layer of negative photoresist on a bottom layer.

Figure 6 is a cross section according to Figure 5 after the formation of the resist structure.

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Figure 7 is a cross section according to Figure 5 showing the irradiation of the photoresist layer.

20 Figure 8 is a cross section according to Figure 6 for a further example.

Figure 9 is a cross section according to Figure 8 after an application of a functional layer.

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Figure 10 is a cross section according to Figure 9 after a partial removal of the functional layer by lift-off.

30 Figure 1 is a top view of a surface 12 of a layer of negative photoresist 2, which is applied on a bottom layer 1. A resist structure 3 that is to be produced from the negative photoresist is indicated in Figure 1 by a rectangular area.

The area of the resist structure 3 may instead comprise any other shape or pattern according to individual requirements, in particular a triangle, a polygon having more than four corners, a circle or an ellipse. The resist structure 3 may
5 comprise a plurality of areas of such shapes, which may be similar or different from one another and may be arranged at equal or different distances from one another. The resist structure 3 may especially be intended as a lift-off mask, which will be used to structure a layer that is deposited on
10 the lift-off mask. The bottom layer 1 may be a semiconductor substrate or wafer, for instance, or a layer that is arranged on or above a substrate. The resist structure 3 that is to be produced from the negative photoresist is surrounded by a border zone 4 within the layer of negative photoresist 2. A
15 width 14 of the border zone 4 is indicated in Figure 1 by arrows.

The border zone 4 is provided with a pattern 5 comprising a dimension that is smaller than a minimal resolution of the
20 irradiation that is intended to produce a locally selective insolubility of the negative photoresist. The pattern 5 is provided to modify the intensity of the radiation reaching different levels below the surface 12 and hence to modify the vertical profile of the solubility of the negative
25 photoresist within the border zone 4 as compared to the vertical profile of the solubility in the centre of the resist structure 3. The pattern 5 is formed within the layer of the negative photoresist 2.

30 Figure 2 is a magnified view of the section indicated in Figure 1 by a dash-dotted contour. The section according to Figure 2 shows an area of the border zone 4 between adjacent areas of the layer of negative photoresist 2, including an

area of the resist structure 3 to be produced. The border zone 4 is provided with a pattern 5. In the example shown in Figure 2, the pattern 5 is a grid-like pattern 5-1 composed of two pluralities of parallel lines, wherein the lines

5 belonging to one of the pluralities are arranged transverse to the lines belonging to the other plurality. The distances between the parallel lines may be typically in the range from 100 nm to 700 nm and may especially be constant, thus forming a grid with constant pitch. A typical example for a suitable
10 pitch is 400 nm in both directions.

Figure 3 is a further magnified view of the section indicated in Figure 1 by a dash-dotted contour, the corresponding areas being designated with the same reference numerals. In the
15 example shown in Figure 3, the pattern 5 is a pattern of parallel lines 5-2. The distances between the parallel lines may be typically in the range from 100 nm to 700 nm and may especially be constant, thus forming an array with constant pitch. A typical example for a suitable pitch is 400 nm.

20 Figure 4 is still a further magnified view of the section indicated in Figure 1 by a dash-dotted contour, the corresponding areas being designated with the same reference numerals. In the example shown in Figure 4, the pattern 5 is
25 a pattern of contact holes 5-3. The holes are not provided for contacts, but they can be shaped and produced in a way that is similar to the formation of small via holes. The holes may be arranged in a random distribution, or they may be arranged on a regular pattern at equal intervals. Such a
30 regular pattern may typically comprise a pitch in the range from 100 nm to 700 nm, which may especially be constant. The diameters of the holes may typically be in the range from 200 nm to 400 nm and may be different or equal.

Figure 5 is a cross section showing the layer of negative photoresist 2 on the upper surface 11 of the bottom layer 1. The position of this cross section is indicated in Figure 1 by the dash-dotted straight lines. Figure 5 shows the region of the resist structure 3 to be produced and the border zone 4, which surrounds the resist structure 3 and is therefore present at both lateral boundaries of the resist structure 3. The width 14 of the border zone 4 is again indicated by arrows. The layer of negative photoresist 2 is irradiated, in particular illuminated by light that is incident on the upper surface 12.

The pattern 5 of the border zone 4 is preferably designed like a sub-resolution assist feature (SRAF). Contrary to conventional sub-resolution assist features, the pattern 5 is used in a completely different way for the formation of the resist structure 3, in particular by an illumination with a conventional imaging system like a stepper, for instance. The dimensions of the resist structure 3 are larger than the resolution limit of the imaging system. The pattern 5 comprises a dimension or a structural feature that is smaller than the resolution limit of the imaging system. Because of the different dimensions, the structure of the pattern 5 is not reproduced in detail, but only the general outline of the resist structure 3 is transferred to the layer of negative photoresist 2. The porosity or the voids of the pattern 5 allow a larger radiation dose to reach a certain level below the surface 12 and thus to cross-link and harden the negative photoresist in the border zone 4 down to deeper levels below the surface 12 than in the central region surrounded by the border zone 4. The region where the sidewall of the resist structure 3 will be located is thus modified.

The radiation intensity in the vertical direction through the layer of negative photoresist 2 is controlled in the border zone 4 by setting the relevant dimensions of the pattern 5 to appropriate values. In the example of the pattern of contact holes 5-3, the diameter of the holes and the pitch of their array, for instance, are relevant parameters that can be adapted. During the irradiation of the negative photoresist, the radiation dose should be set to be sufficiently high to secure a full cross-linking of the negative photoresist in the border zone 4 down to the bottom layer 1. If a full cross-linking is thus achieved in the border zone 4, the subsequent developing process will stop exactly at the position where the negative photoresist is thoroughly cross-linked down to the bottom layer 1, independently of the amount of developer employed. Therefore the shape and size of the sidewall undercut can be adapted to the requirements of individual applications by setting the relevant parameters, especially the width 14 of the border zone 4.

Figure 6 is a cross section according to Figure 5 after the formation of the resist structure 3 with an overhanging sidewall 6. Other profiles of the sidewall 6, like the one shown in Figure 8, can also be produced by adapting the width 14 of the border zone 4 and the structure of the pattern 5.

The upper edge of the resist structure 3 overhangs the upper surface 11 of the bottom layer 1, and the reentrant shape of the sidewall 6 is appropriate for an application of the resist structure 3 as a lift-off mask.

Figure 7 is a cross section according to Figure 5 showing the irradiation of the layer of negative photoresist 2. The layer of negative photoresist 2 is shielded against the radiation by a mask 7 covering the region outside the surface area 13

- 12 -

where the resist structure 3 is to be produced. The radiation is indicated in Figure 7 by the arrows pointing down. Below the uncovered surface area 13, the radiation penetrates into the negative photoresist. The radiation intensity is a
5 function of the distance D from the surface 12 and decreases with increasing distance D. The irradiation is preferably performed in such a way as to render the negative photoresist insoluble in the border zone 4 down to the bottom layer 1.

10 Figure 8 is a cross section according to Figure 6, which shows the produced resist structure 3 after the developing process and after the removal of that portion of the layer of negative photoresist 2 that has not been irradiated. In the example shown in Figure 8, the negative slope of the sidewall
15 6 is essentially at a constant angle with the plane of the surface 11. The resist structure 3 according to Figure 8 is also appropriate for an application as a lift-off mask.

A constant slope of the sidewall 6 can be produced by
20 adopting a suitable pattern 5. In the example of Figure 4, using a pattern of contact holes 5-3, the diameters of the contact holes can be varied in the direction across the border zone 4, i. e. in the direction following one of the small arrows inserted in Figure 1, so that the translucency
25 of the pattern 5 comprises a gradient in that direction. In other examples in which the pattern 5 comprises a plurality of lines running parallel to the boundary of the border zone 4, the distances between the lines can be varied accordingly.

30 Figures 9 and 10 illustrate a lift-off process using the resist structure 3. A layer 8, which may be provided for a function of a semiconductor device and will therefore be designated as functional layer 8 in the following, is applied

covering the entire surface 11. As the sidewall 6 of the resist structure 3 is undercut, the functional layer 8 is not deposited conformally at the sidewall 6, but is interrupted at the sharp upper edge, thus forming a gap. The portion of the functional layer 8 that is applied on the resist structure 3 can therefore easily be removed by removing the resist structure 3, without affecting the remaining portion 9, as shown in Figure 10.

The described method uses only negative photoresist, which has an excellent temperature stability, and avoids the disadvantages of producing a double resist layer. In this method the shape of the undercut sidewall does not depend as much on the developing process as in conventional

photolithographic methods. The thorough cross-linking in the region of the sidewall facilitates the control of the undercut and allows narrower design rules than heretofore.

Since the attack of the developer is inhibited at the position where the resist is cross-linked down to the bottom layer, the developing process can be performed until the resist is completely removed from the surface area outside the resist structure without affecting the undercut.

Furthermore, there is no restriction with respect to a minimal size of the undercut. These properties allow the

sidewall of the resist structure to be easily adapted to any existing topographies. Pattern effects are minimized, and the developing process can be extended to avoid scumming in open surface areas and sticking of subsequently deposited layers.

The method is not limited to T-shaped sidewall profiles. By varying the pattern in the border zone, the areal image intensity can be modified to meet the requirements of a specific application, and vertical reentrant structures can

be produced that cannot be realized with conventional methods. Feature degradation due to thermal treatment is low, because only cross-linked portions of the photoresist remain after developing, and no stabilizing flood exposure will be
5 necessary.

List of reference numerals

- 1 bottom layer
- 2 layer of negative photoresist
- 5 3 resist structure
- 4 border zone
- 5 pattern
- 5-1 grid-like pattern
- 5-2 pattern of parallel lines
- 10 5-3 pattern of contact holes
- 6 sidewall
- 7 mask
- 8 functional layer
- 9 remaining portion of the functional layer
- 15 10 surface area of the bottom layer
- 11 surface of the bottom layer
- 12 surface of the layer of negative photoresist
- 13 surface area of the layer of the negative photoresist
- D distance from the surface

Claims

1. Method of producing a resist structure, comprising:
 - applying a layer of a negative photoresist (2) on a
5 bottom layer (1),
 - irradiating a surface area (13) of the layer of the negative photoresist (2) according to the resist structure (3) to be produced, and
 - removing the layer of the negative photoresist (2)
10 outside the irradiated surface area (13), thus forming the resist structure (3),characterized in that
 - the layer of the negative photoresist (2) is provided with a pattern (5) formed within the layer of the
15 negative photoresist (2) in a border zone (4) of the resist structure (3) before it is irradiated, the pattern (5) comprising a dimension or structural feature that is smaller than a minimal resolution of the irradiation.
- 20 2. The method of claim 1, wherein the pattern (5) is provided as a sub-resolution assist feature.
3. The method of claim 1 or 2, further comprising:
 - at least one dimension characterizing the pattern (5),
25 and a width (14) of the border zone (4), the dimension of the pattern (5) being smaller than one tenth of the width (14) of the border zone (4).
4. The method of one of claims 1 to 3, wherein the pattern
30 (5) comprises a plurality of elements having the same dimensions.

- 17 -

5. The method of claim 4, wherein the dimensions of the elements are smaller than one tenth of a width (14) of the border zone (4).
- 5 6. The method of claim 4 or 5, wherein the elements are arranged in a regular array with constant pitch.
7. The method of claim 6, wherein the pitch is smaller than one tenth of a width (14) of the border zone (4).
- 10 8. The method of one of claims 1 to 7, wherein the pattern (5) is a gridlike pattern (5-1).
- 15 9. The method of one of claims 1 to 7, wherein the pattern (5) is a pattern of parallel lines (5-2).
10. The method of one of claims 1 to 7, wherein the pattern (5) is a pattern of contact holes (5-3).
- 20 11. The method of one of claims 1 to 10, wherein the resist structure (13) is produced with an undercut sidewall (6).
12. The method of one of claims 1 to 11, wherein
- 25 the resist structure (13) is produced as a lift-off mask.

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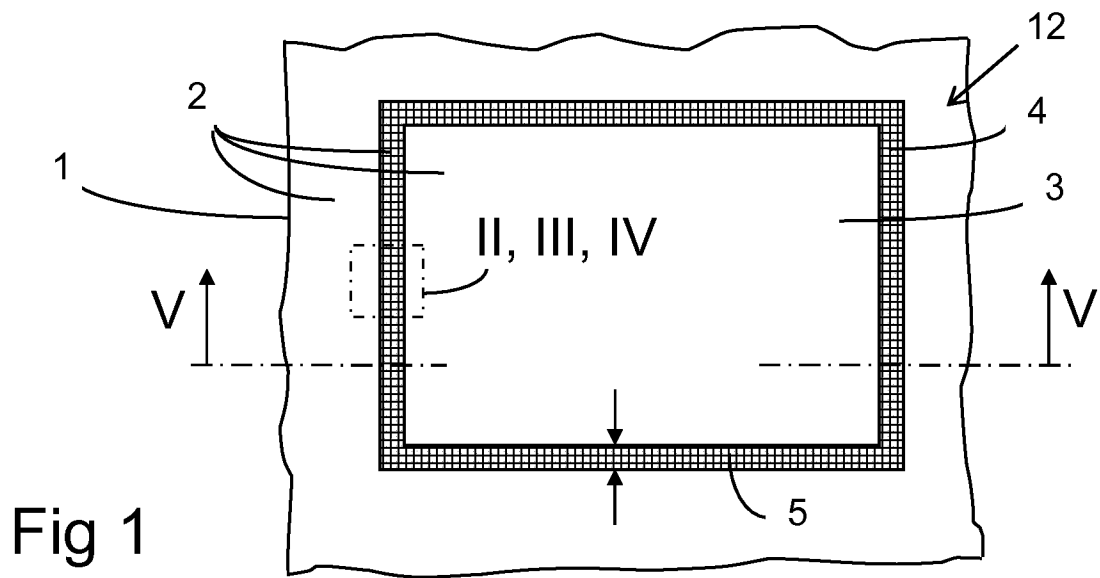


Fig 1

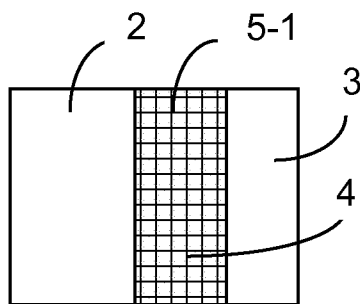


Fig 2

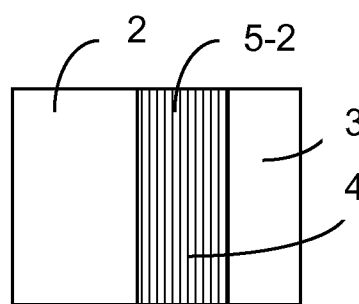


Fig 3

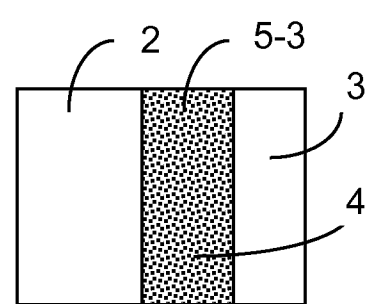


Fig 4

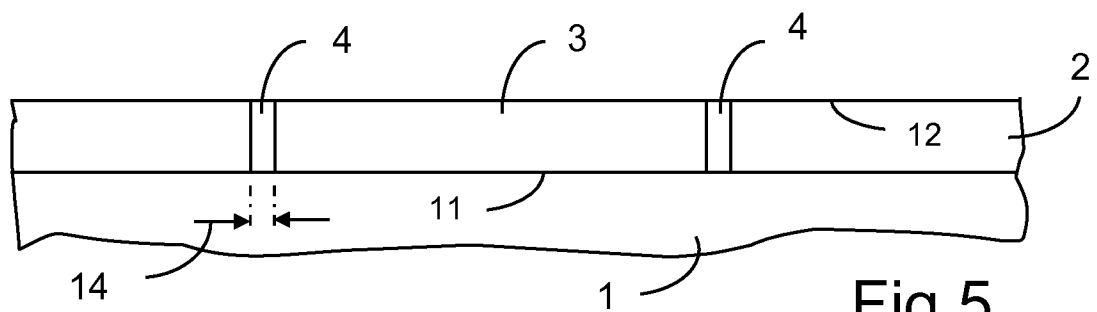


Fig 5

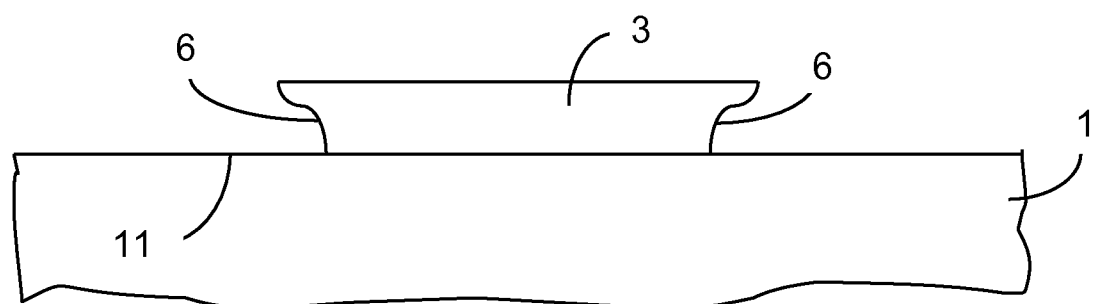
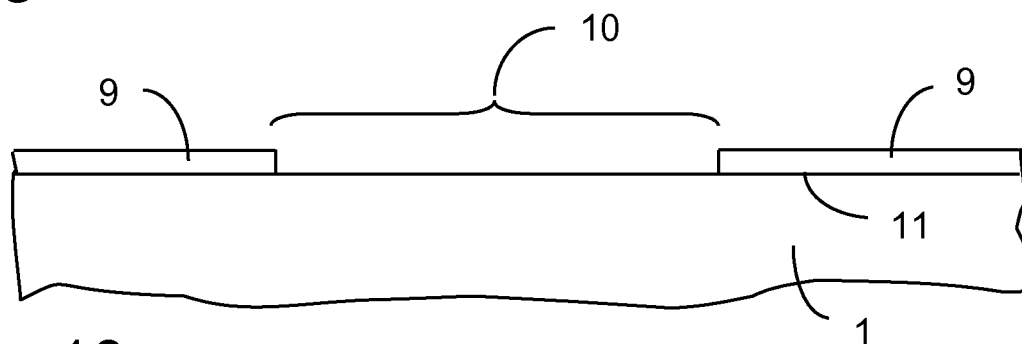
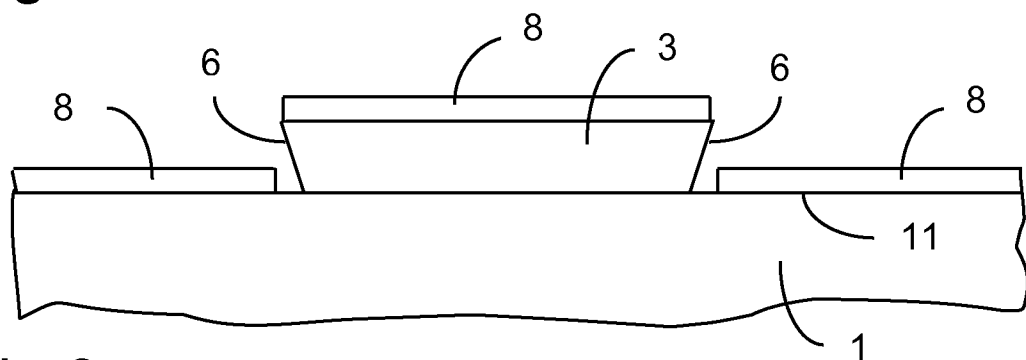
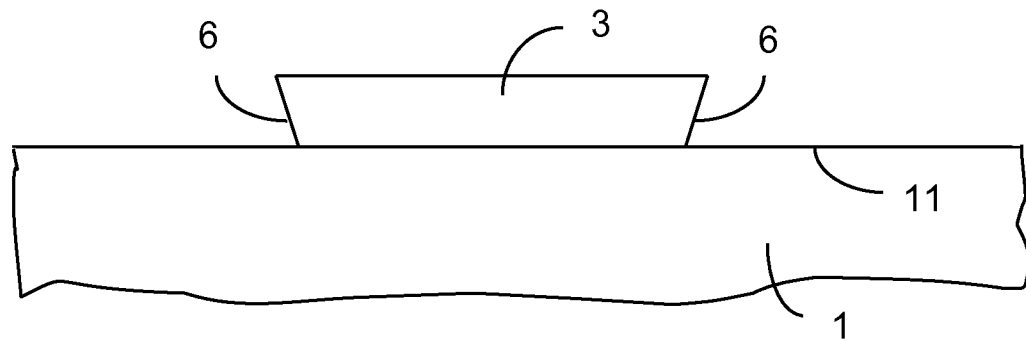
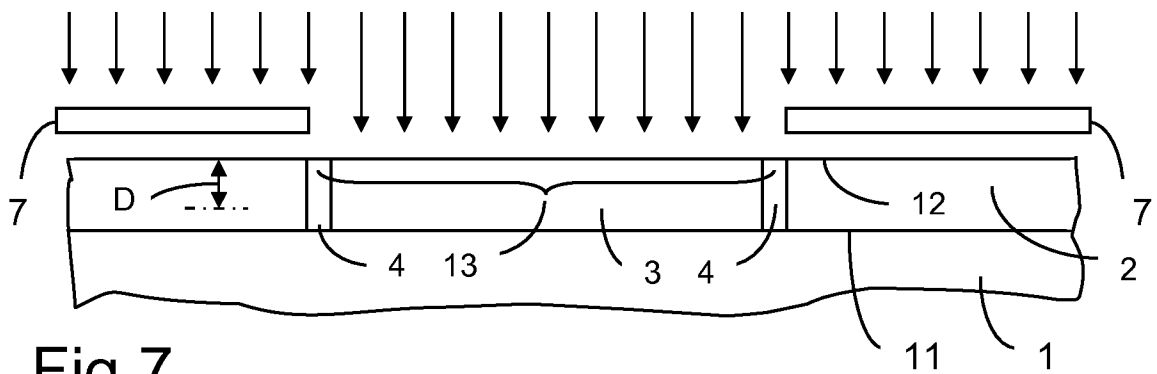


Fig 6

2/2



INTERNATIONAL SEARCH REPORT

International application No
PCT/EP2014/066081

A. CLASSIFICATION OF SUBJECT MATTER
INV. G03F1/54 G03F7/16
ADD.

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
G03F

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

EPO-Internal, INSPEC, WPI Data, COMPENDEX

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	WARREN W. FLACK ET AL: "Highly re-entrant profiles in a thick photosensitive material for nanotechnology applications", PROCEEDINGS OF SPIE, vol. 6153, 9 March 2006 (2006-03-09), page 61534I, XP055093511, ISSN: 0277-786X, DOI: 10.1117/12.655721 paragraph [03.2]; figure 1 ----- -/-	1-12



Further documents are listed in the continuation of Box C.



See patent family annex.

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Date of the actual completion of the international search

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19/09/2014

Name and mailing address of the ISA/

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Fax: (+31-70) 340-3016

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Haenisch, Ulrich

INTERNATIONAL SEARCH REPORT

International application No
PCT/EP2014/066081

C(Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	HYUNG SUK LEE ET AL: "A simple and effective lift-off with positive photoresist; A simple and effective lift-off with positive photoresist", JOURNAL OF MICROMECHANICS & MICROENGINEERING, INSTITUTE OF PHYSICS PUBLISHING, BRISTOL, GB, vol. 15, no. 11, 1 November 2005 (2005-11-01), pages 2136-2140, XP020091417, ISSN: 0960-1317, DOI: 10.1088/0960-1317/15/11/020 figure 1	1-12
A	----- FEELY W E: "Microplastic structures", PROCEEDINGS OF THE SPIE - THE INTERNATIONAL SOCIETY FOR OPTICAL ENGINEERING USA, vol. 631, 1986, pages 48-61, XP002718100, ISSN: 0277-786X page 49; figures 4,7	1-12
A	----- US 5 698 377 A (SEINO TATSUYA [JP]) 16 December 1997 (1997-12-16)	1-12
A	----- JP S60 135949 A (MATSUSHITA ELECTRIC WORKS LTD) 19 July 1985 (1985-07-19)	1-12

INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No

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Patent document cited in search report		Publication date	Patent family member(s)	Publication date
US 5698377	A	16-12-1997	JP H08339958 A US 5698377 A	24-12-1996 16-12-1997

JP S60135949	A	19-07-1985	NONE	
